

#### 80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BVDSS	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	7mΩ @ V <sub>GS</sub> = 10V	68A
80V	10.5mΩ @ V <sub>GS</sub> = 6V	56A

### **Description**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

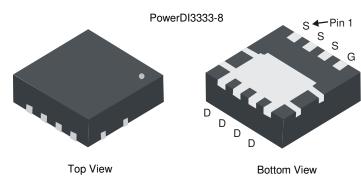
### **Features and Benefits**

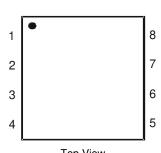
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Low Rds(ON) Ensures On-State Losses are Minimized
- Excellent Qgd × RDS(ON) Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH8008SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

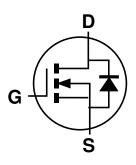
https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)







Top View Pin-Out

**Equivalent Circuit** 

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMTH8008SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



HZ8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	80	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	$T_C = +25$ °C $T_C = +100$ °C	lD	68 48	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		l <sub>D</sub>	17 12	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	68	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	272	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =	I <sub>SM</sub>	272	Α	
Avalanche Current, L = 1mH (Note 8)	las	18.7	Α	
Avalanche Energy, L = 1mH (Note 8)	Eas	174.85	mJ	

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	125	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	46	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	PD	50	W
Thermal Resistance, Junction to Case (Note 7)		Rejc	3.0	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

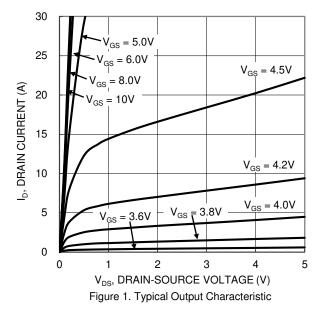
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	80	_	_	V	VGS = 0V, ID = 1mA	
Zero Gate Voltage Drain Current	IDSS		1	1	μA	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	,						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2		4	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Static Drain-Source On-Resistance			5.0	7	mΩ	Vgs = 10V, ID = 14A	
Static Drain-Source On-nesistance	Rds(on)		7.1	10.5		VGS = 6V, ID = 12A	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 14A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		1945			V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	750	_	pF		
Reverse Transfer Capacitance	Crss	_	45.8	_			
Gate Resistance	$R_g$	_	1.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 5V)	Qg	_	18.4	_		V <sub>DS</sub> = 40V, I <sub>D</sub> = 14A	
Total Gate Charge (VGS = 10V)	Qg	_	31.7	_	nC		
Gate-Source Charge	Q <sub>gs</sub>		8.3		IIC		
Gate-Drain Charge	Qgd	_	8.6	_			
Turn-On Delay Time	tD(ON)	-	9.2			$V_{DD} = 40V$ , $V_{GS} = 10V$ , $I_{D} = 14A$ , $R_{G} = 6\Omega$	
Turn-On Rise Time	tR		11.8				
Turn-Off Delay Time	tD(OFF)		27.0		ns		
Turn-Off Fall Time	tF	_	17.3	_			
Body Diode Reverse Recovery Time	trr	_	40.6	_	ns	1 440 -11/-14 - 1000///	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		50.9		nC	$I_S = 14A$ , di/dt = 100A/ $\mu$ s	

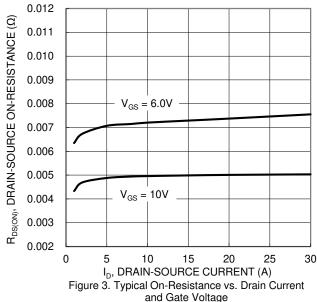
Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.









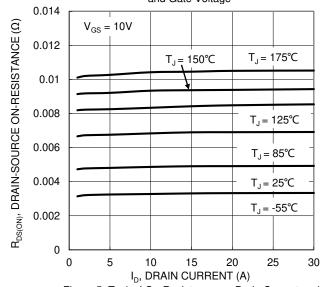
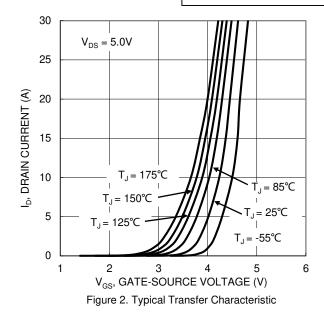
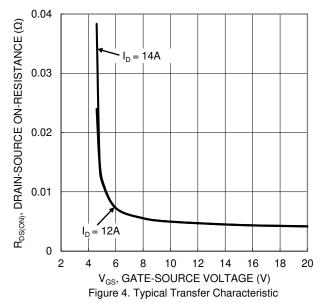


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





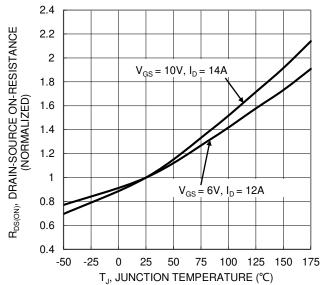


Figure 6. On-Resistance Variation with Temperature





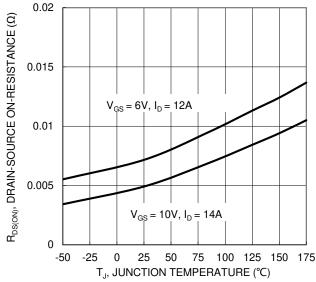


Figure 7. On-Resistance Variation with Temperature

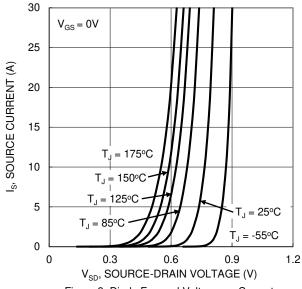


Figure 9. Diode Forward Voltage vs. Current

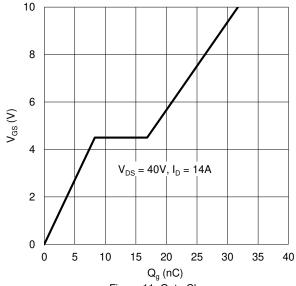


Figure 11. Gate Charge

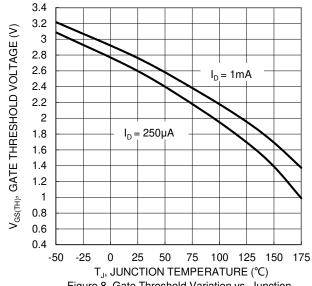
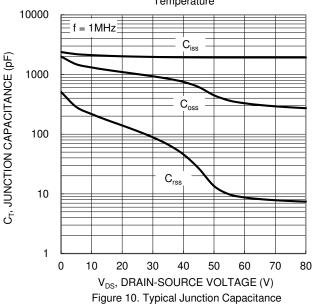


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R<sub>DS(ON)</sub> 100 ID, DRAIN CURRENT (A) 10 w = 10ms T<sub>C</sub> = 25°C Single Pulse  $P_{W} = 100 \text{ms}$ DUT on Infinite Heatsink  $V_{GS} = 10V$ 0.01 100 1000 0.1 10 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

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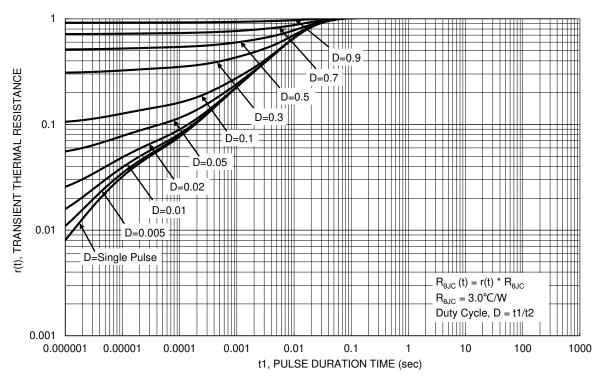


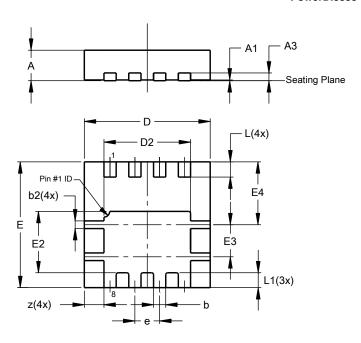
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8

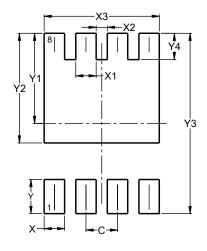


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
<b>A3</b>	_	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
z	_	_	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)			
С	0.650			
X	0.420			
X1	0.420			
X2	0.230			
Х3	2.370			
Υ	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			
Y4	0.540			



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